

TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

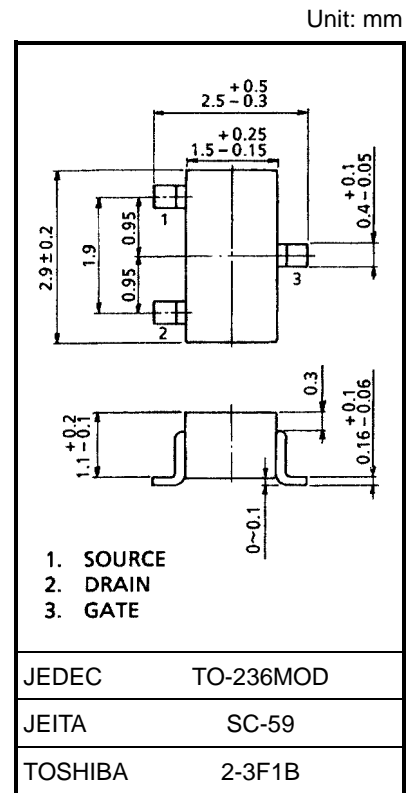
# 2SK368

Audio Frequency and High Voltage Amplifier Applications  
Constant Current Applications

- High breakdown voltage:  $V_{GDS} = -100$  V (min)
- High input impedance:  $I_{GSS} = -1.0$  nA (max) ( $V_{GS} = -80$  V)
- Small package

### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	$V_{GDS}$	-100	V
Gate current	$I_G$	10	mA
Drain power dissipation	$P_D$	150	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55~125	$^\circ\text{C}$



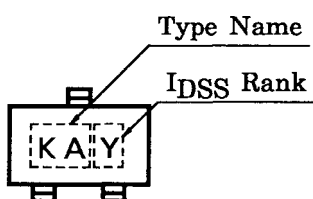
Weight: 0.012 g (typ.)

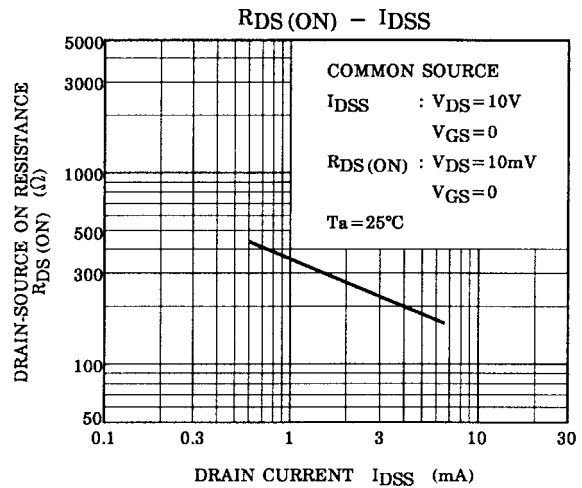
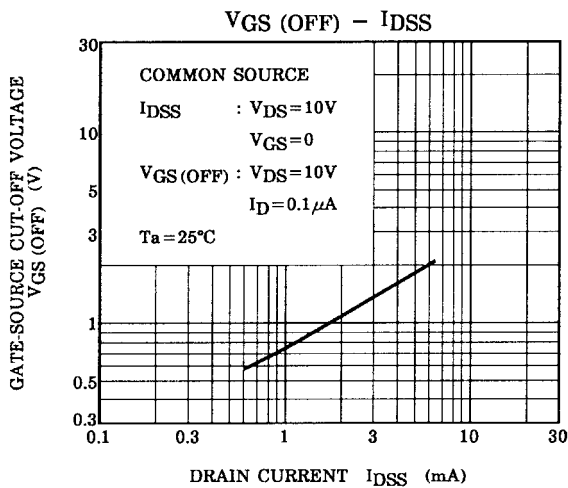
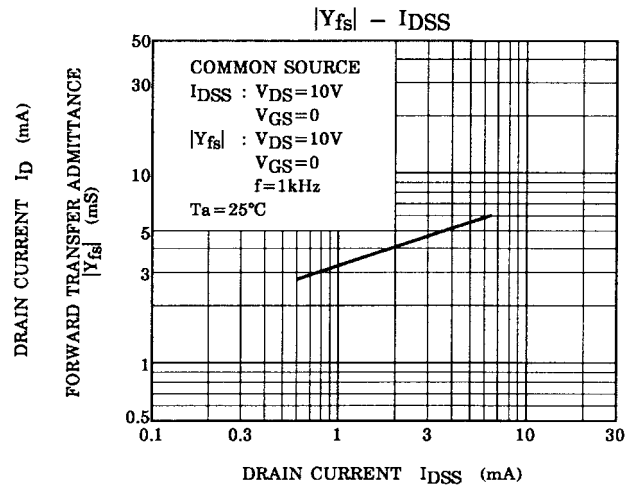
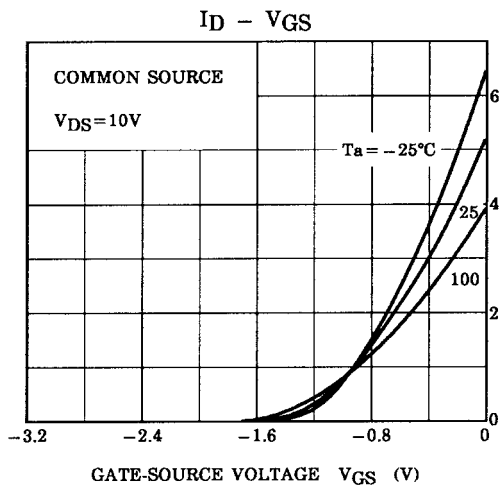
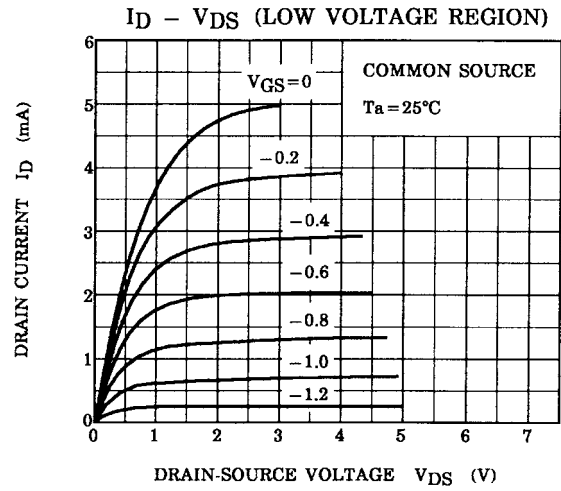
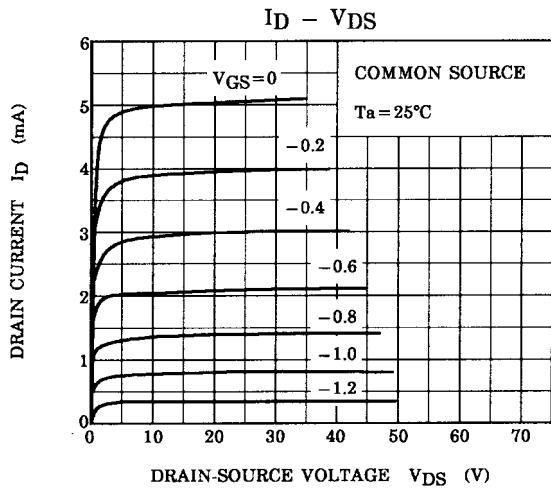
### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

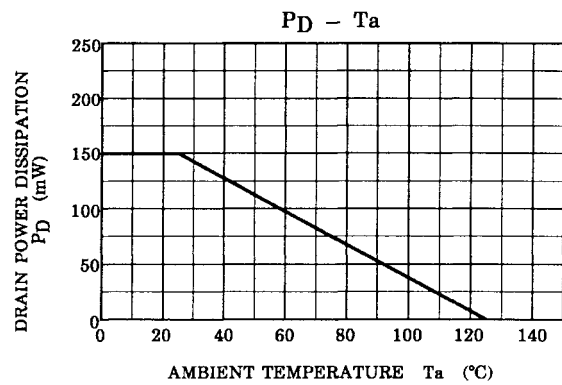
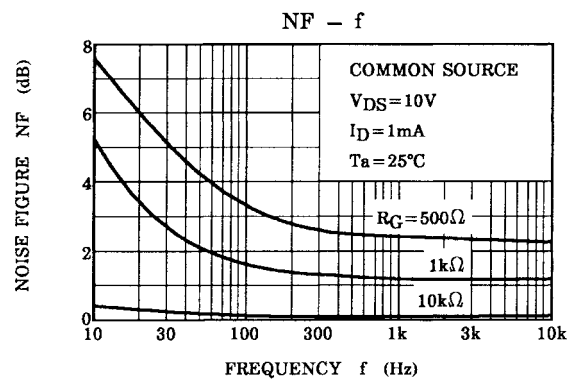
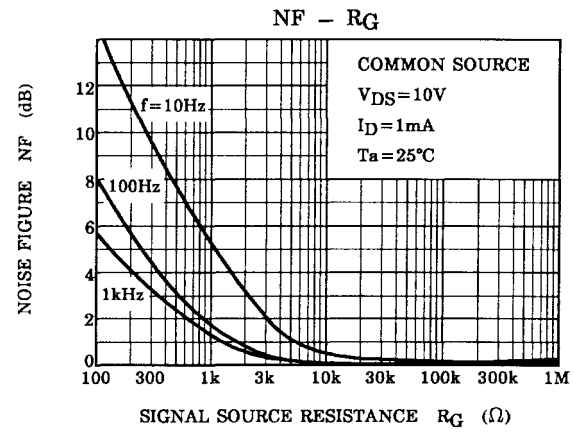
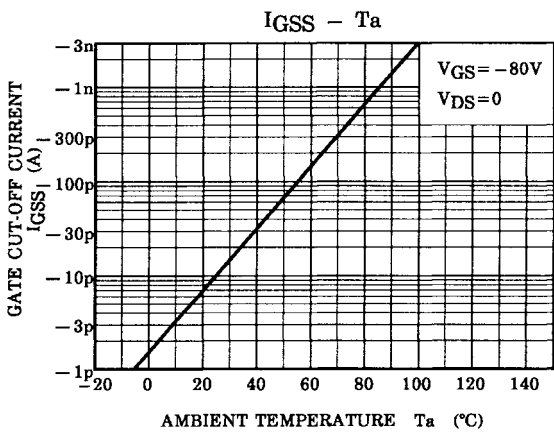
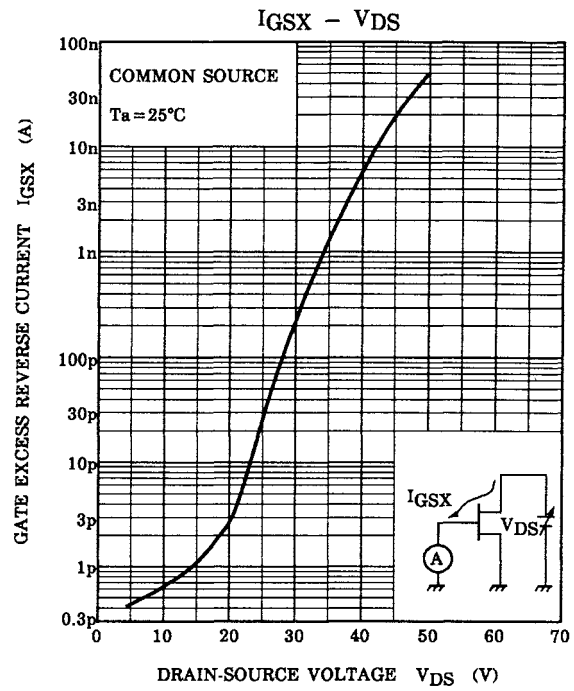
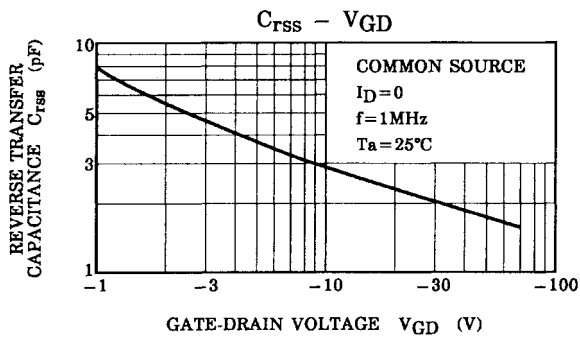
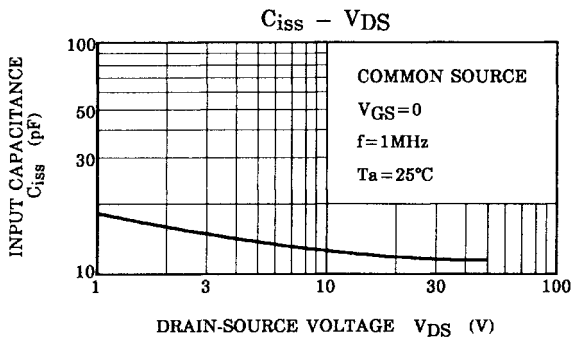
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate cut-off current	$I_{GSS}$	$V_{GS} = -80$ V, $V_{DS} = 0$	—	—	-1.0	nA
Gate-drain breakdown voltage	$V_{(BR) GDS}$	$V_{DS} = 0$ , $I_G = -100$ $\mu\text{A}$	-100	—	—	V
Drain current	$I_{DSS}$ (Note)	$V_{DS} = 10$ V, $V_{GS} = 0$	0.6	—	6.5	mA
Gate-source cut-off voltage	$V_{GS (OFF)}$	$V_{DS} = 10$ V, $I_D = 0.1$ $\mu\text{A}$	-0.4	—	-3.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10$ V, $V_{GS} = 0$ , $f = 1$ kHz	1.5	4.6	—	mS
Input capacitance	$C_{iss}$	$V_{DS} = 10$ V, $V_{GS} = 0$ , $f = 1$ MHz	—	13	—	pF
Reverse transfer capacitance	$C_{rss}$	$V_{DG} = 10$ V, $I_D = 0$ , $f = 1$ MHz	—	3	—	pF
Noise figure	NF	$V_{DS} = 10$ V, $V_{GS} = 0$ $R_G = 100$ k $\Omega$ , $f = 100$ Hz	—	0.5	—	dB

Note:  $I_{DSS}$  classification O: 0.6~1.4 mA, Y: 1.2~3.0 mA, GR (G): 2.6~6.5 mA

### Marking







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